

## K. Memory (Design & Process Technology) 분과

2020년 2월 13일(목), 09:00-10:30 / Room G (스페이드 II+III, 6층)

### ■ [TG1-K] Devices for Neuromorphic Computing I

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<b>TG1-K-1</b> 09:00-09:30	<p>[초청]</p> <p><b>On-Chip Trainable Analog Phase Change Memory (PCM) Synaptic Array for Spiking Restricted Boltzmann Machine (RBM)</b></p> <p>SangBum Kim</p> <p><i>Department of Materials Science and Engineering, Seoul National University</i></p>
<b>TG1-K-2</b> 09:30-09:45	<p><b>Synaptic Device Failure Analysis of Array-Based Neuromorphic System Using Sigmoidal TS Neuron</b></p> <p>Wooseok Choi, Donguk Lee, and Hyunsang Hwang</p> <p><i>Center for Single Atom-based Semiconductor Device and the Department of MS&amp;E, POSTECH</i></p>
<b>TG1-K-3</b> 09:45-10:00	<p><b>Influence of Al<sub>2</sub>O<sub>3</sub> Insertion Layer on RS/Retention Characteristics in IGZO Memristor for Neuromorphic Application</b></p> <p>Woo Sik Choi, Jun Tae Jang, Jungi Min, Donguk Kim, Sung-Jin Choi, Dong Myong Kim, and Dae Hwan Kim</p> <p><i>School of Electrical Engineering, Kookmin University</i></p>
<b>TG1-K-4</b> 10:00-10:15	<p><b>Training and Operation of an Artificial Neural Network in IGZO-based Crossbar Array</b></p> <p>Jun Tae Jang, Jungi Min, Woo Sik Choi, Donguk Kim, Jingyu Park, Sung-Jin Choi, Dong Myong Kim, and Dae Hwan Kim</p> <p><i>School of Electrical Engineering, Kookmin University</i></p>
<b>TG1-K-5</b> 10:15-10:30	<p><b>MOSFET Compensated Synapse Device for Analog Neuromorphic System</b></p> <p>Chuljun Lee, Myungjun Kim, Yubin Song, and Daeseok Lee</p> <p><i>Department of Electronic Materials Engineering, Kwangwoon University</i></p>